



# Bipolar NPN Bare Die – BTN009

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## Part Description

The BTN009 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

## Key Parameters:

- VCBO = 60V
- VCEO = 40V
- VEBO = 6V
- hFE = 100-300 @ VCE = 10V, IC = 0.15A
- VCE(Sat) = 1V @ IC = 0.5A, IB = 50mA
- fT = 250 MHz @ VCE = 20V, IE = 0A
- COBO = 8pF @ VCB = 10V

## Features

Designed to provide performance equivalent to FAIRCHILD / ON SEMI MMBT4401, 2N4401, MMBT2222A or 2N2222A

## Die Size (Unawn)

350 $\mu$ m X 350 $\mu$ m, 14 Mils X 14 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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